

02-11-03

15:58

FROM-RatnerPrestia

6104070701

T-353 P.006/016 F-704

YAO-3950

PATENT

#21/17 (NE)
2/26/3
Suresh
Suresh
5/2/3

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

Applicant: Yoshihisa Nagano et al.

: Art Unit: 2815

Serial No.: 09/103,873

: Examiner: J. Diaz

Filed: June 24, 1998

Expedited Procedure

For: SEMICONDUCTOR DEVICE AND METHOD
FOR FABRICATING THE SAME

37 C.F.R. § 1.116

AMENDMENT

FAX RECEIVED

FEB 11 2003

Assistant Commissioner for Patents
Washington, DC 20231

TECHNOLOGY CENTER 2800

S I R :

Responsive to the Official Action dated September 24, 2002, please
amend the above-identified application as follows:

CLAIMS:

Please cancel claims 3 and 5.

Please replace claims 1 and 32 with the following amended claims:

1. (As Amended) A semiconductor device, comprising:

a capacitor provided on a supporting substrate having an integrated
circuit thereon and including a lower electrode, a dielectric film, and an upper
electrode, said dielectric film being formed from either a dielectric material having a
high dielectric constant or a ferroelectric material;

a first interlayer insulating film provided so as to directly cover the
capacitor;

a first interconnect selectively provided on the first interlayer
insulating film and electrically connected to the integrated circuit and the capacitor
through a first contact hole formed in the first interlayer insulating film;

DLM_IYA03950AMEND07.DOC